

MOSFETs Silicon N-Channel MOS (DTMOSIV)

# **TK20N60W5**

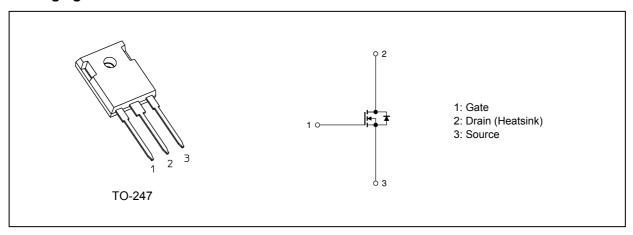
#### 1. Applications

· Switching Voltage Regulators

#### 2. Features

- (1) Fast reverse recovery time:  $t_{rr} = 110 \text{ ns (typ.)}$
- (2) Low drain-source on-resistance:  $R_{DS(ON)}$  = 0.15  $\Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (3) Easy to control Gate switching
- (4) Enhancement mode:  $V_{th}$  = 3 to 4.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

#### 3. Packaging and Internal Circuit



# 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                     | Symbol   | Rating           | Unit       |       |
|-------------------------------------|----------|------------------|------------|-------|
| Drain-source voltage                |          | V <sub>DSS</sub> | 600        | V     |
| Gate-source voltage                 |          | V <sub>GSS</sub> | ±30        |       |
| Drain current (DC)                  | (Note 1) | I <sub>D</sub>   | 20         | Α     |
| Drain current (pulsed)              | (Note 1) | I <sub>DP</sub>  | 80         |       |
| Power dissipation (T <sub>c</sub> = | = 25°C)  | P <sub>D</sub>   | 165        | W     |
| Single-pulse avalanche energy       | (Note 2) | E <sub>AS</sub>  | 200        | mJ    |
| Avalanche current                   |          | I <sub>AR</sub>  | 5          | Α     |
| Reverse drain current (DC)          | (Note 1) | I <sub>DR</sub>  | 20         |       |
| Reverse drain current (pulsed)      | (Note 1) | I <sub>DRP</sub> | 80         |       |
| Channel temperature                 |          | T <sub>ch</sub>  | 150        | ů     |
| Storage temperature                 |          | T <sub>stg</sub> | -55 to 150 |       |
| Mounting torque                     |          | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    |                       | 0.757 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 14 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max   | Unit |
|--------------------------------|----------------------|---|-----|------|-------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±1    | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V    | _   | _    | 100   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 600 | _    | _     | V    |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA     | 3   | _    | 4.5   |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A     | _   | 0.15 | 0.175 | Ω    |

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1800 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub>   |   | _   | 5.5  | _   |      |
| Output capacitance             | C <sub>oss</sub>   |   | _   | 45   | _   |      |
| Effective output capacitance   | C <sub>o(er)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V       | _   | 70   | _   |      |
| Gate resistance                | r <sub>g</sub>     | V <sub>DS</sub> = OPEN, f = 1 MHz                         | _   | 1.5  | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>     | See Figure 6.2.1  | _   | 45   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>    |   | _   | 90   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>     |   | _   | 6    | _   |      |
| Switching time (turn-off time) | t <sub>off</sub>   |   | _   | 100  | _   |      |
| MOSFET dv/dt ruggedness        | dv/dt              | V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 10 A       | 50  | _    |     | V/ns |

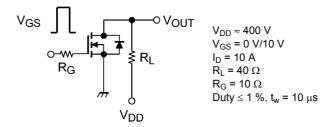


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ |     | 55   |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   | _   | 17   | _   |      |
| Gate-drain charge                               | $Q_{gd}$         |   |     | 33   |     |      |

# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition   | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V                          | _   | _    | -1.7 | V    |
| Reverse recovery time         | t <sub>rr</sub> | I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V                          |     | 110  | 176  | ns   |
| Reverse recovery charge       | $Q_{rr}$        | -dI <sub>DR</sub> /dt = 100 A/μs                                       | _   | 0.6  | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> |  |     | 10   | _    | Α    |
| Diode dv/dt ruggedness        | dv/dt           | I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 400 V | 50  | _    | _    | V/ns |



# 7. Marking

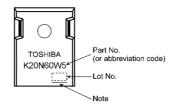


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Rev.3.0

### 8. Characteristics Curves (Note)

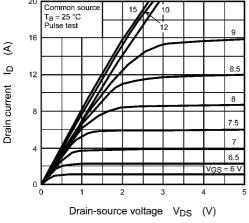
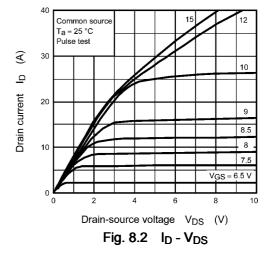


Fig. 8.1  $I_D - V_{DS}$ 



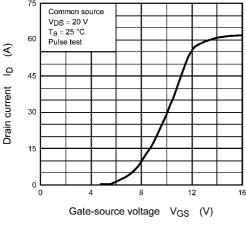


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

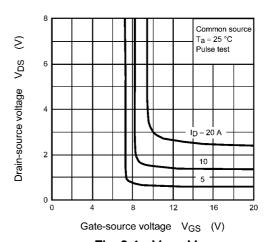


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

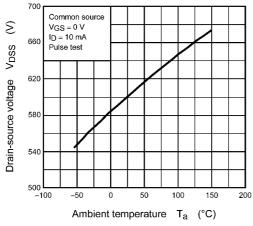


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

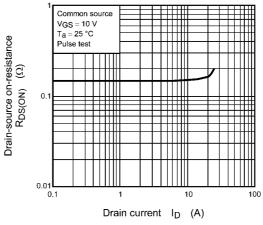


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

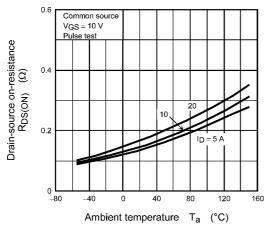
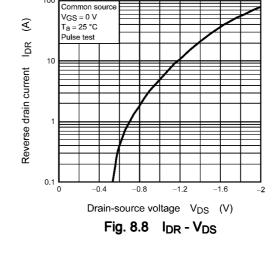


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>



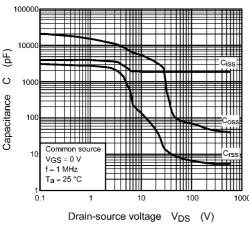


Fig. 8.9 C - V<sub>DS</sub>

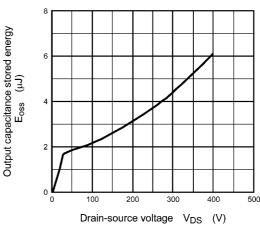


Fig. 8.10 Eoss - V<sub>DS</sub>

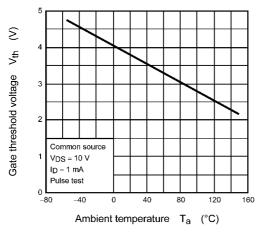


Fig. 8.11 V<sub>th</sub> - T<sub>a</sub>

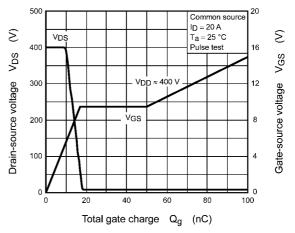


Fig. 8.12 Dynamic Input/Output Characteristics

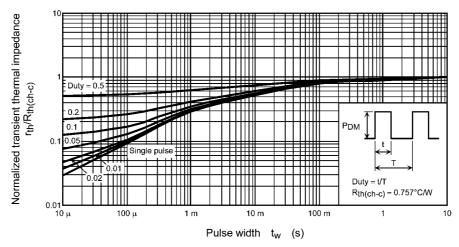


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

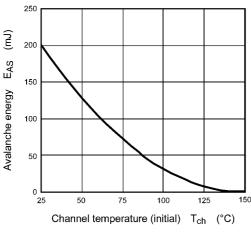


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

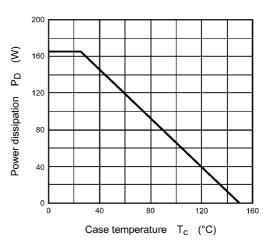


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

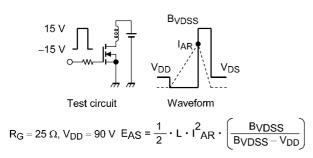


Fig. 8.16 Test Circuit/Waveform

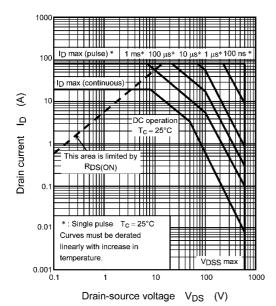


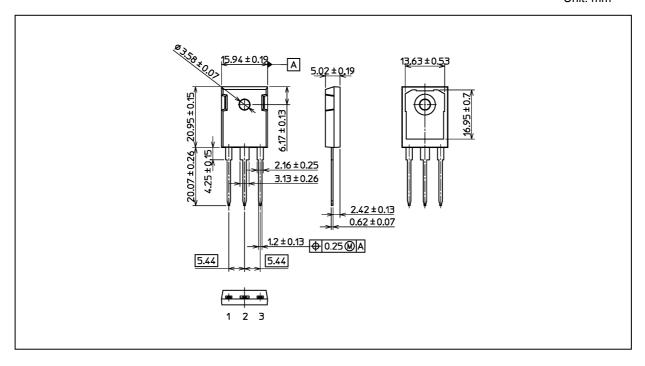
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 6.15 g (typ.)

|                  | Package Name(s) |
|------------------|-----------------|
| JEITA: SC-65     |                 |
| TOSHIBA: 2-16L1A |                 |
| Nickname: TO-247 |                 |



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